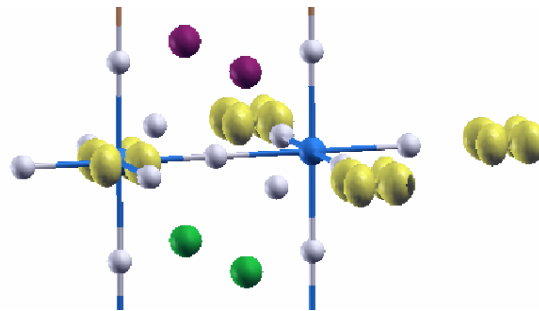


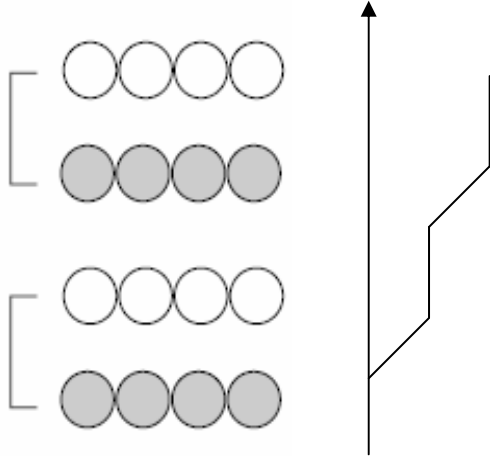
Manipulating electronic states at oxide surfaces and interfaces

R. Pentcheva

Ludwig-Maximilians-University, Munich



Type 3: $Q \neq 0$, $\mu \neq 0$

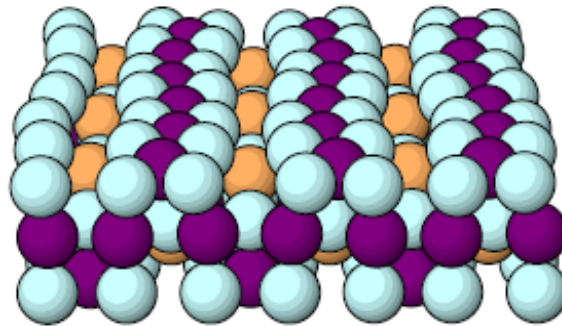


Stabilization
mechanisms:

- ionic model (*Tasker, 1979*) – *diverging surface energy* – **polarization catastrophe**
- autocompensation rule (*LaFemina, 1994*)
- **strong changes in surface stoichiometry**
surface (atomic) reconstruction/facetting
- structural and electronic relaxations
- **strong modification of electronic structure:**
electronic relaxations, surface states,
metallization: electronic reconstruction
(Noguera, JPCM. 12, 2000, Okamoto and Millis, Nature 2004)
- TM oxides: further mechanisms, e.g.
correlation driven e.g. **charge ordering**
- finite size effects

1. Introduction
2. Stabilisation Mechanisms at a Polar Oxide Surface:
 H_2O on $\text{Fe}_3\text{O}_4(001)$
3. Perovskite superlattices (SL) and thin films
 - $\text{LaAlO}_3/\text{SrTiO}_3$ SL: the n-type interface
 - finite size effects in LaAlO_3 films on $\text{SrTiO}_3(001)$
4. Summary

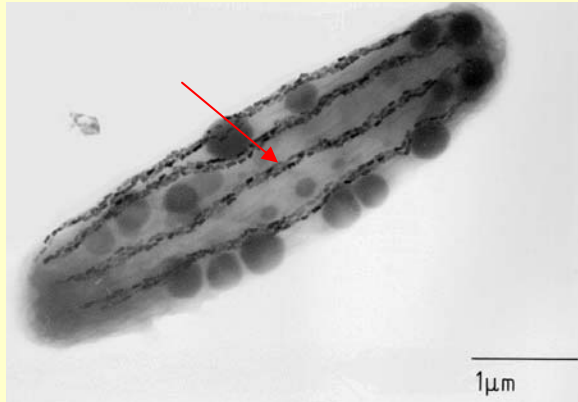
2. Stabilisation Mechanism at a polar Oxide Surface: $\text{Fe}_3\text{O}_4(001)$



paleomagnetism

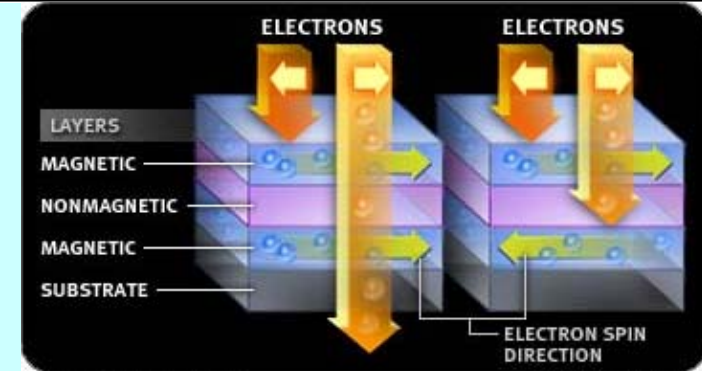


Biom mineralisation (magnetotactic Bacterium)



Hanzlik, Winklhofer, Petersen, JMMM, 248, 258-67 (2002)

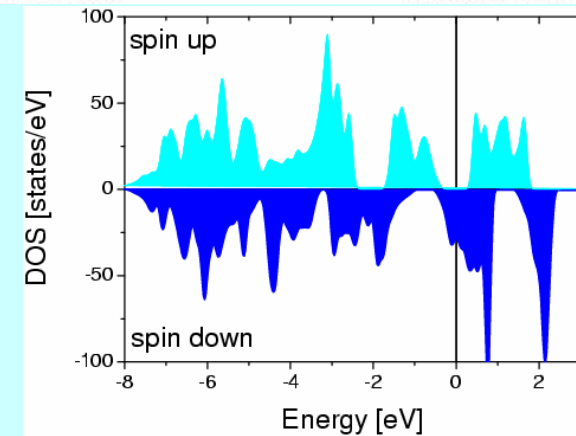
Spintronics



Source: Institute of Physics

Ken Delerich / MSNBC

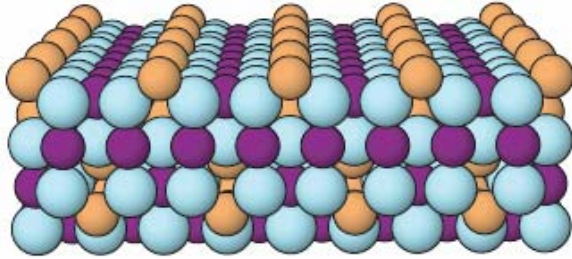
Fe_3O_4 :



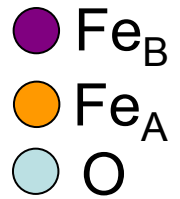
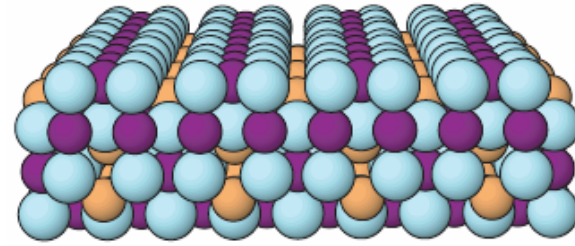
- halfmetal behavior
(Zhang&Satpathy, PRB44, '91)
- high Curie Temperature: 858K
⇒ potential material for spintronics-
devices (Eerenstein et al., PRL88 ,2002)

Fe₃O₄(001): bulk truncations

A-Termination



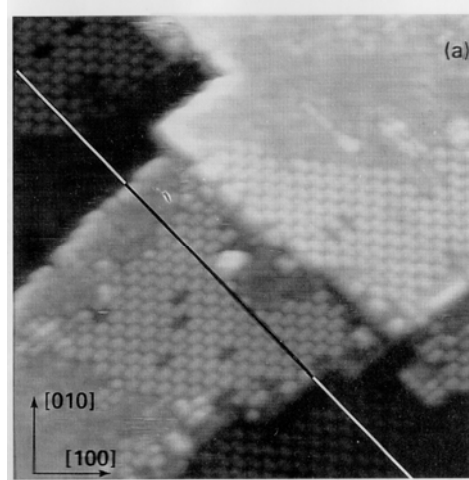
B-Termination



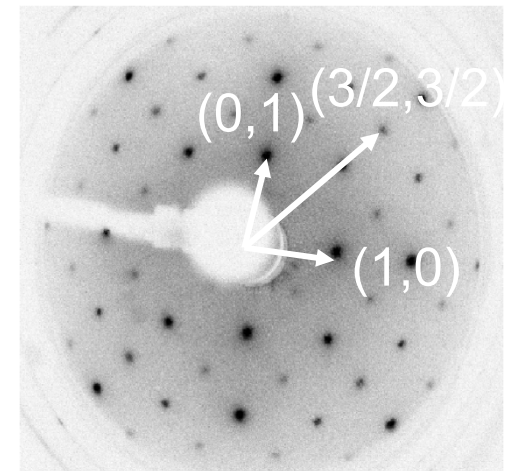
Both bulk terminations – polar Type 3 (*Tasker, 1979*)
 ⇒ discarded based on electrostatic considerations

Experimental results:

$(\sqrt{2} \times \sqrt{2})R45^\circ$ – reconstruction

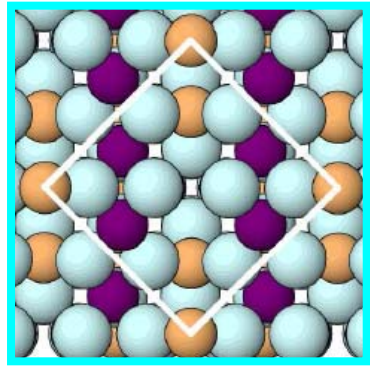


*Gaines et al.,
Surf. Sci. 373 (1997)*

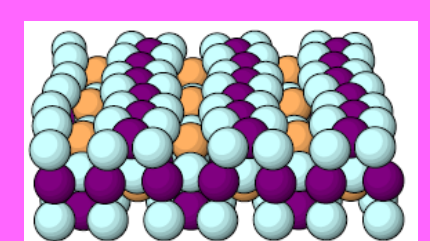
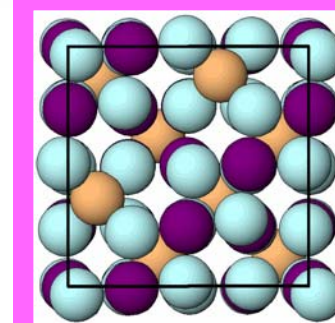
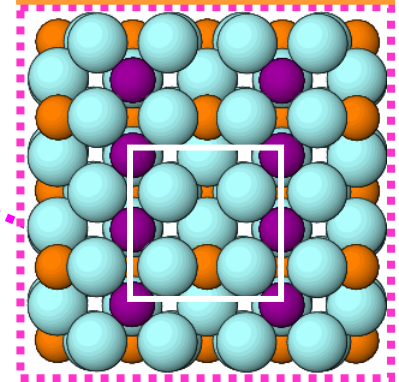
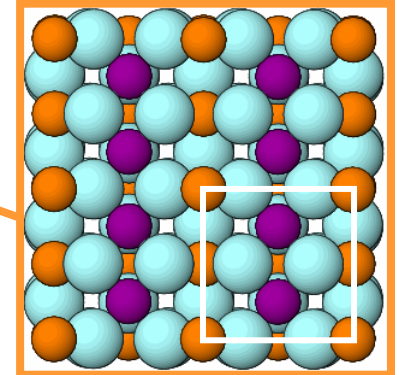
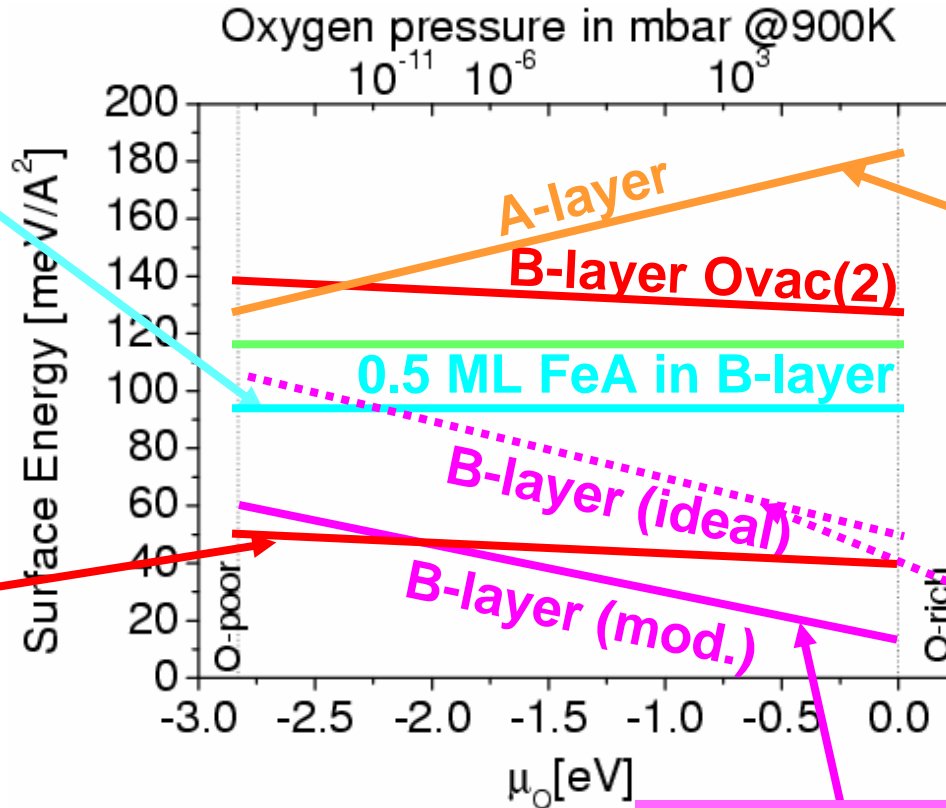
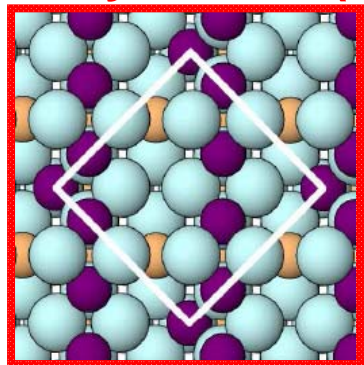


LEED pattern of Fe₃O₄(001)
annealed in UHV at 900 K

Surface Phase Diagram of $\text{Fe}_3\text{O}_4(001)$:



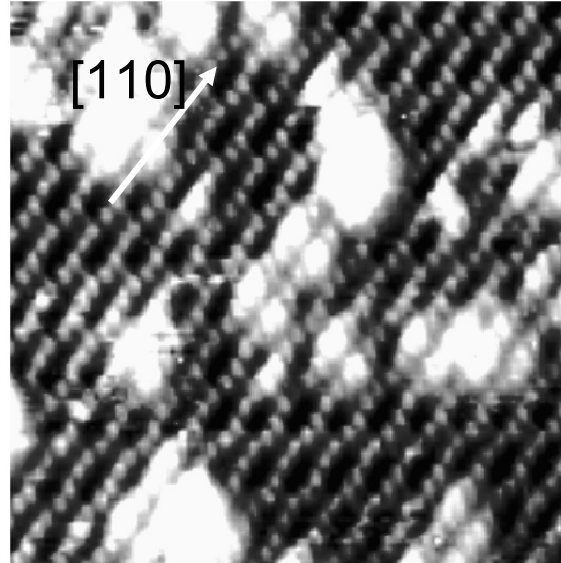
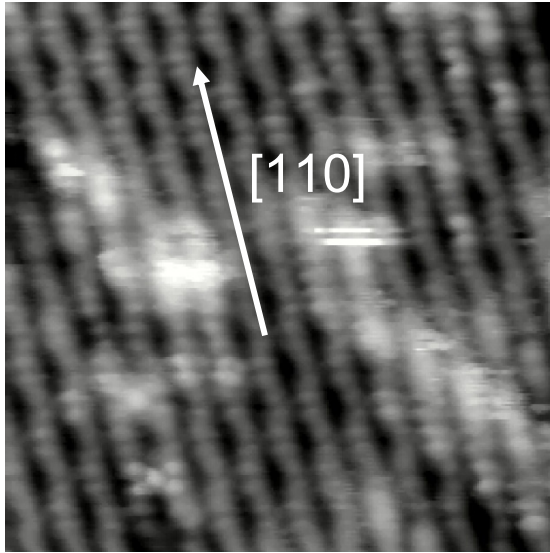
B-layer Ovac(1)



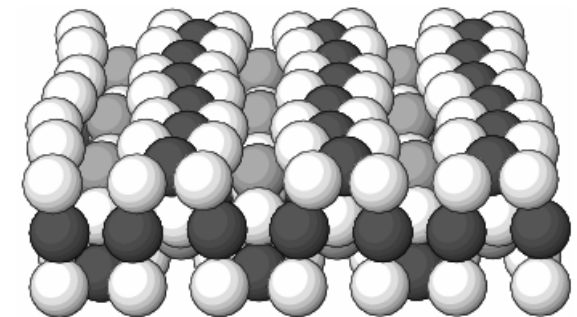
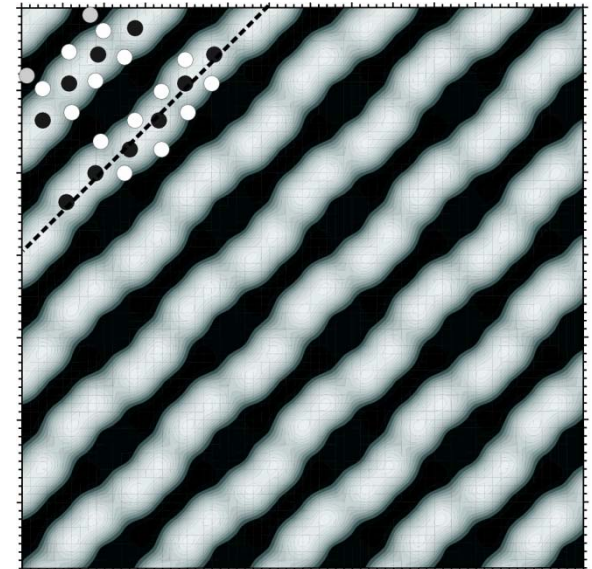
symmetry reduction through lateral and vertical distortions!

Pentcheva, et al. , PRL94,126101,2005

Experiment



Theorie



Fonin, RP et al.,
PRB72, 104436 (2005).

100Åx100 Å, 0.6V, 0.3nA
Stanka et al., SS 448, 2000

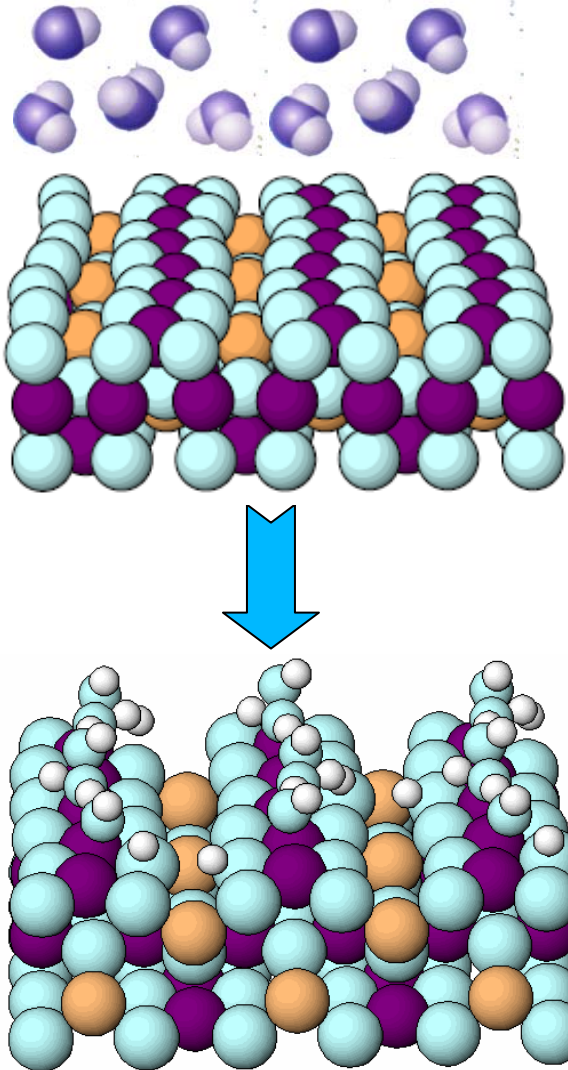
100Åx100 Å, 1.1V, 1.2 nA

- wave-like structure along [110]-direction

Adsorption of H₂O on Fe₃O₄(001)

Applications:

- Adsorption and reduction of heavy metals like As(V), Cd(IV) in aqueous environments
- Water gas phase shift reaction at high temperatures



Questions

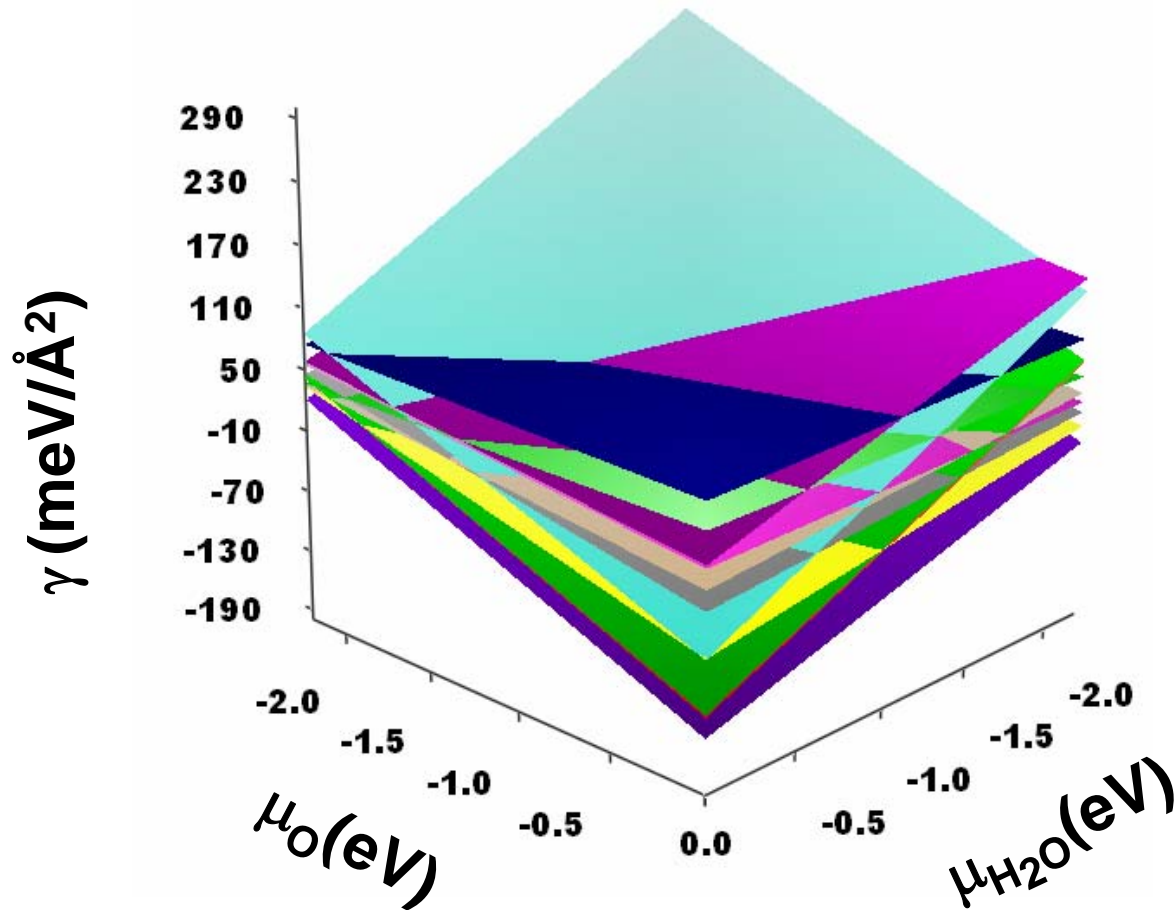
- What is the mode of water adsorption on the magnetite surface?

Molecular vs. Dissociative

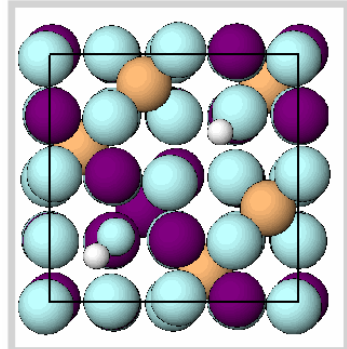
- How does the adsorption affect
 - the surface reconstruction?
 - electronic properties

Surface Phase Diagram

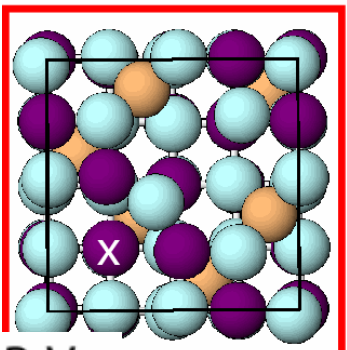
$$\gamma_{Surface} = \gamma(T, P) = \frac{1}{2A} (E_{total} - N_{Fe}\mu_{Fe} - N_O\mu_O - N_H\mu_H)$$



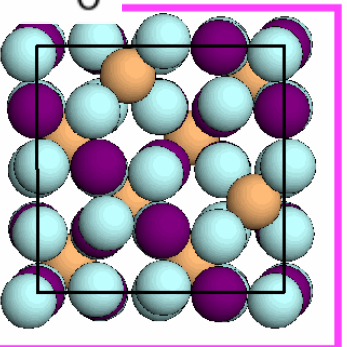
Surface Phase Diagram Bottom View



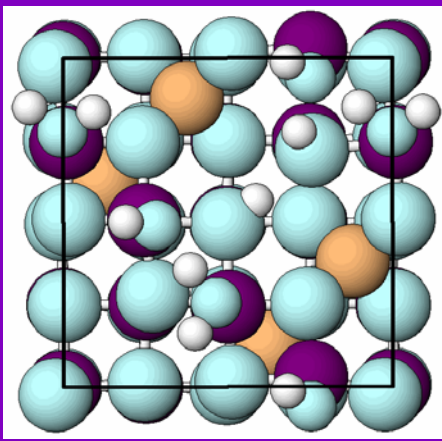
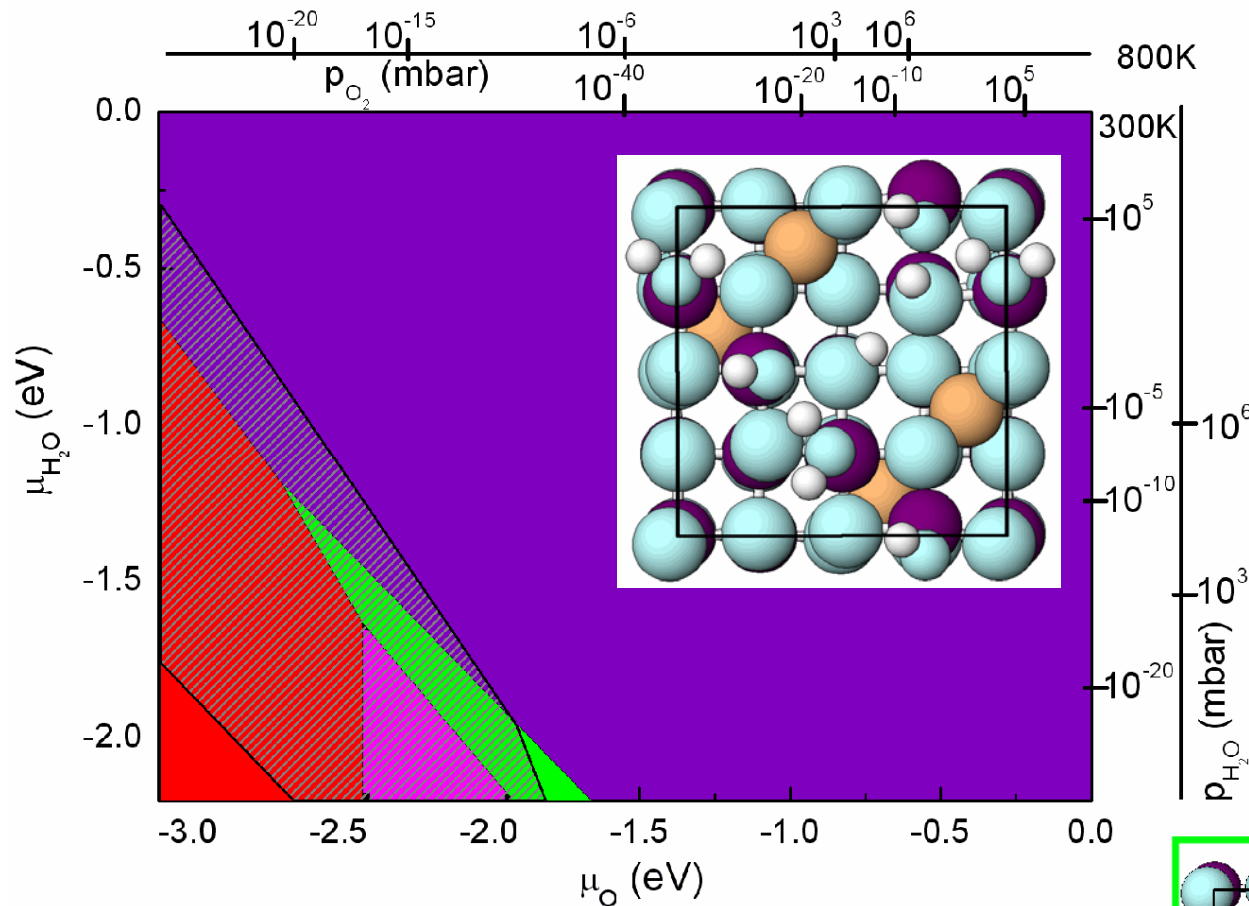
B- $V_O+1H_2O(D)$



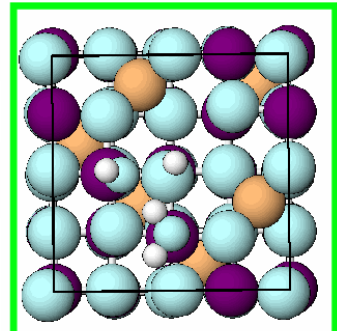
B- V_O

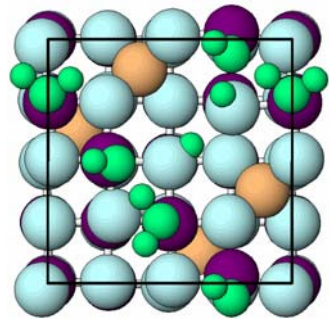


B-layer



B- $2H_2O(M)$



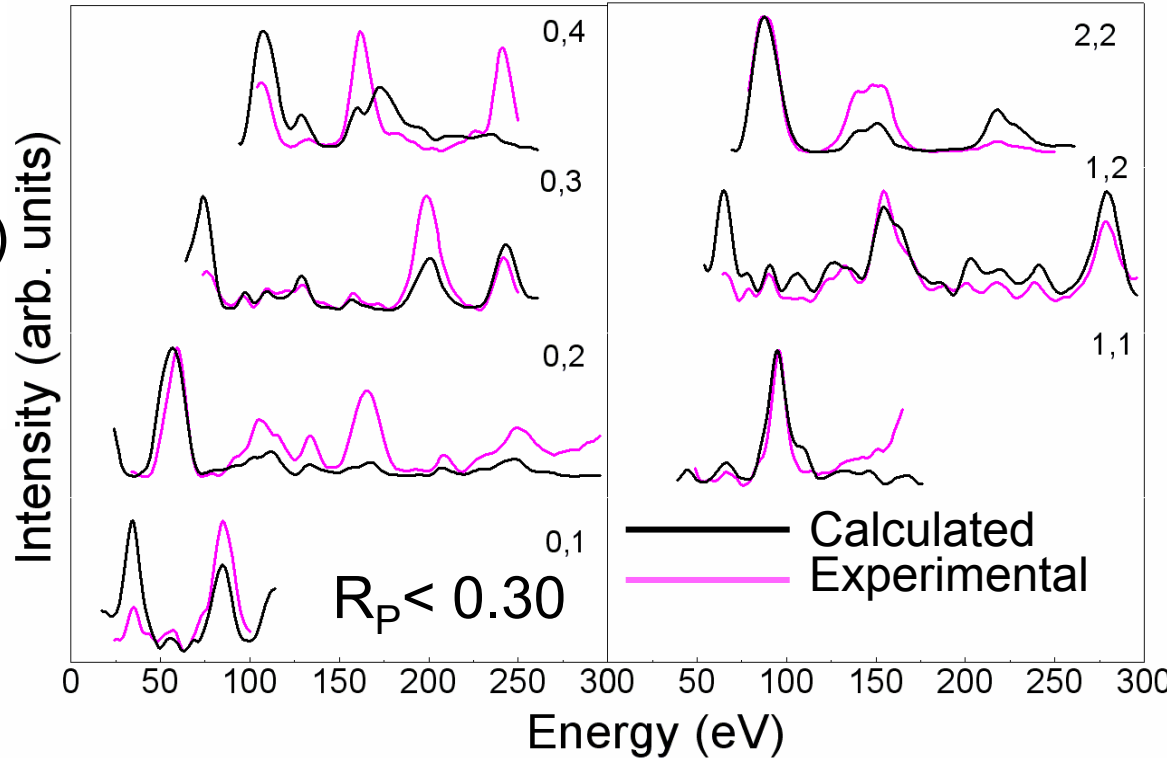
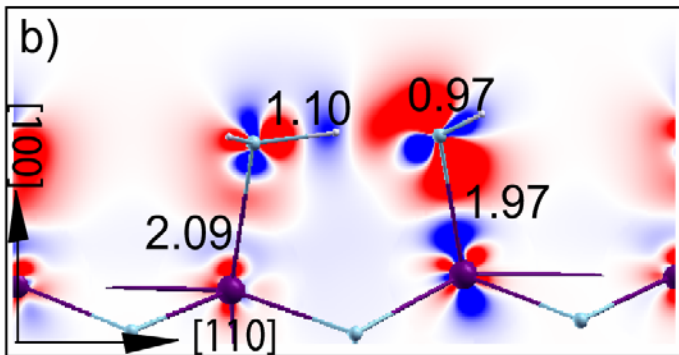


DFT (LEED)

2.09 (2.12)

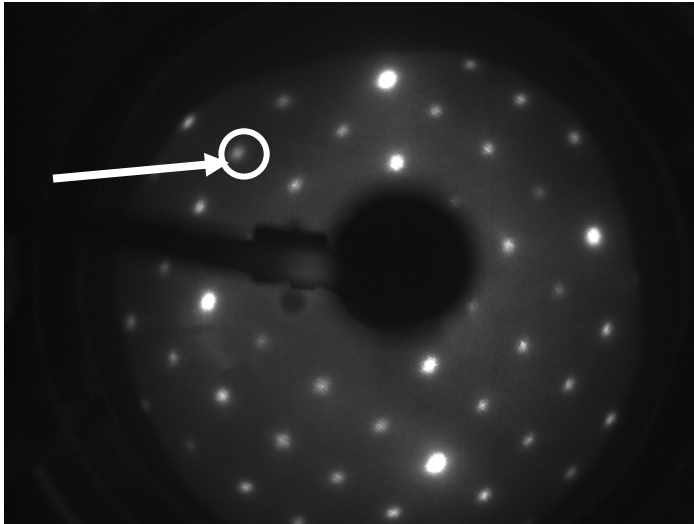
1.97 (1.87)

$\angle \text{HOH } 104.9^\circ$

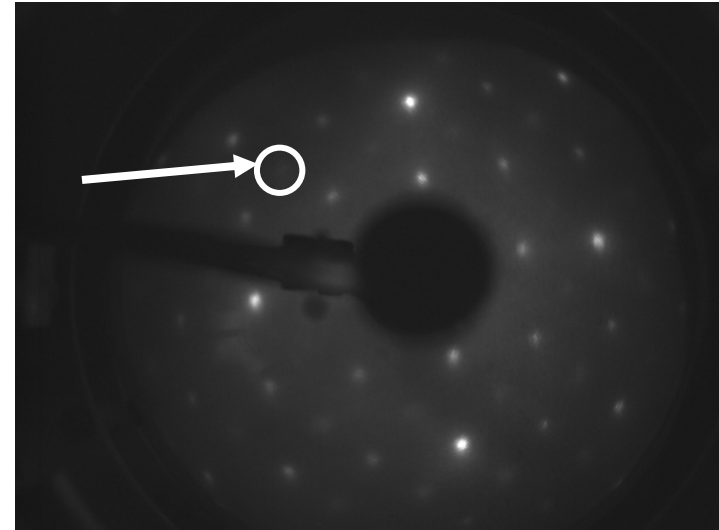


- Two different bond lengths found for $\text{Fe}_B\text{-O}(\text{H}_2\text{O}/\text{OH})$
- Experimental evidence for partial dissociation on the surface
- Partial occupation numbers are found in LEED analysis

LEED Measurements



Before Water Adsorption



After Water Adsorption

Energy of the electron beam is 100.8 eV

Exposure pressure = 1.5×10^{-5} mbar time = 5 mins

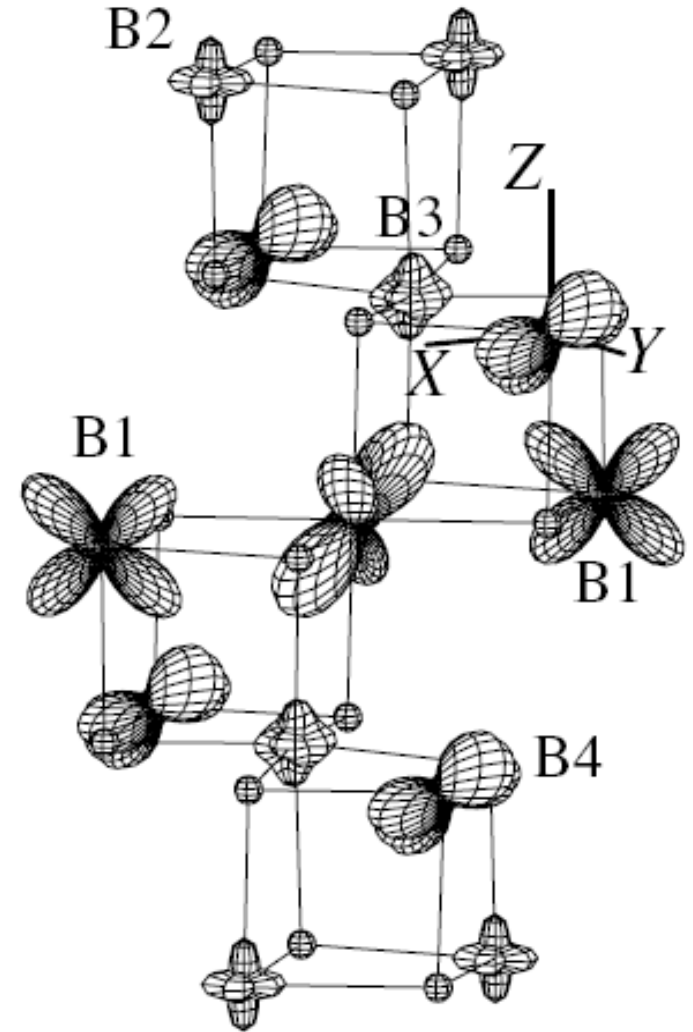
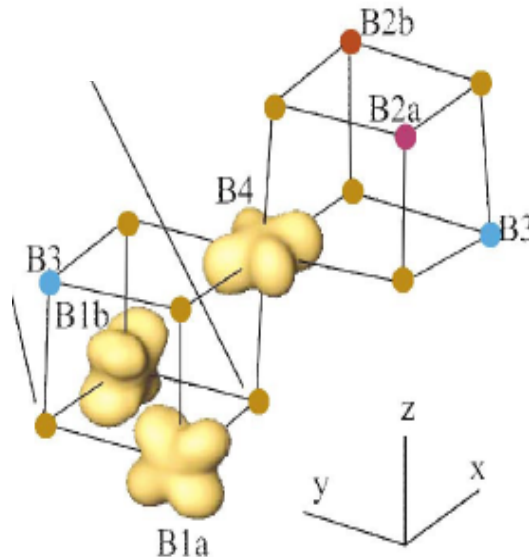
Superstructure spots nearly suppressed

@121-126K Verwey transition
 $\text{Fd}3\text{m} \rightarrow \text{P}2/\text{c}$ (*Wright et al. PRL 2001*)
 $a/\sqrt{2} \times a/\sqrt{2} \times 2a$

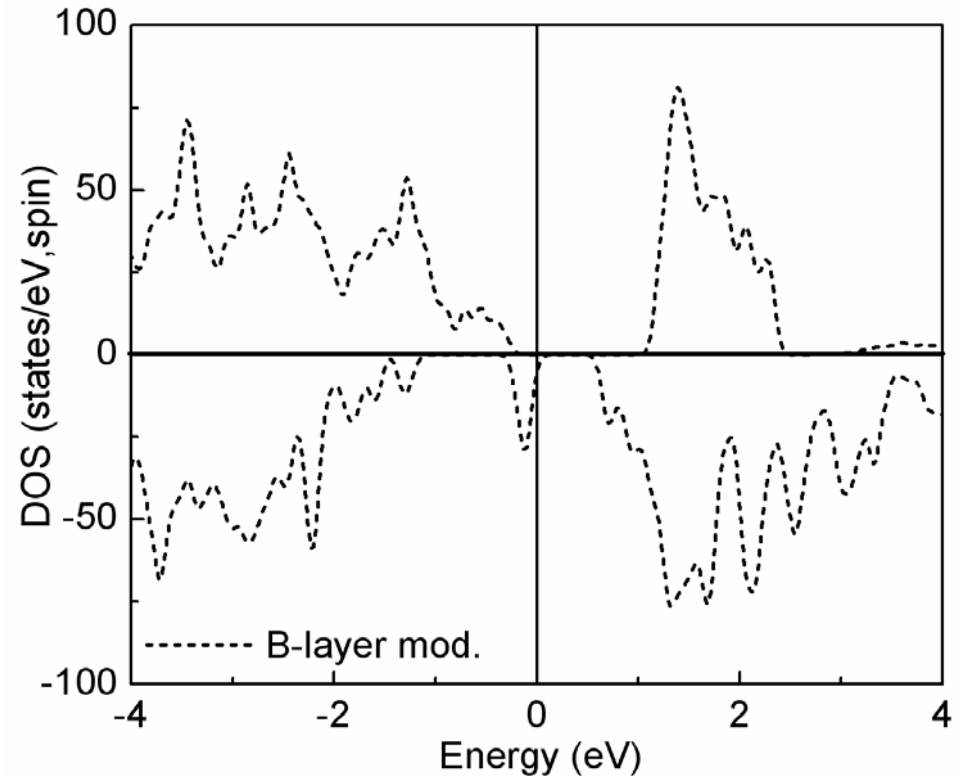
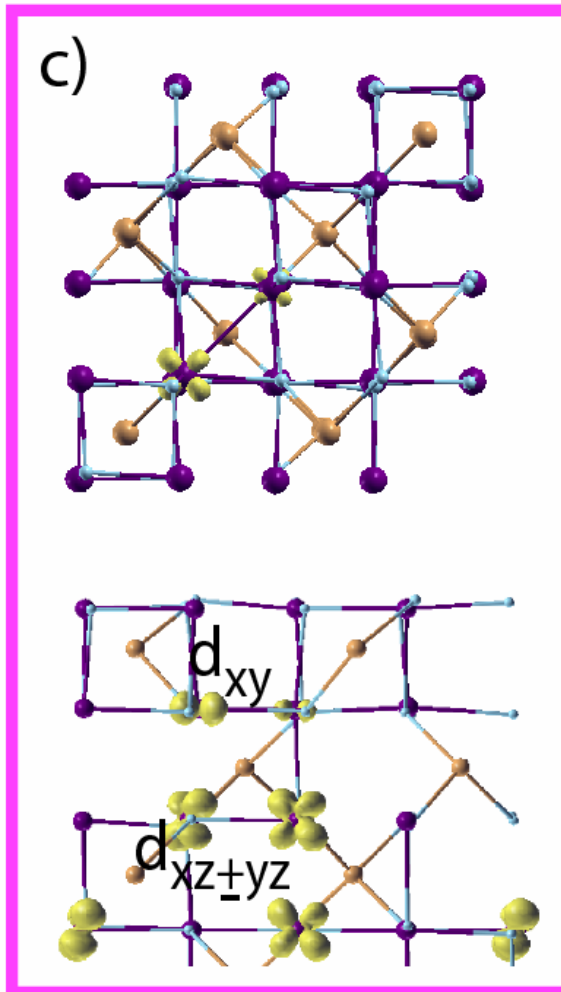
Change in conductivity:
 MIT or semiconductor-
 to-semiconductor

LDA+U: CO/OO
 does not fulfill
 Anderson's
 criterion

Antiferroorbital
 ordering

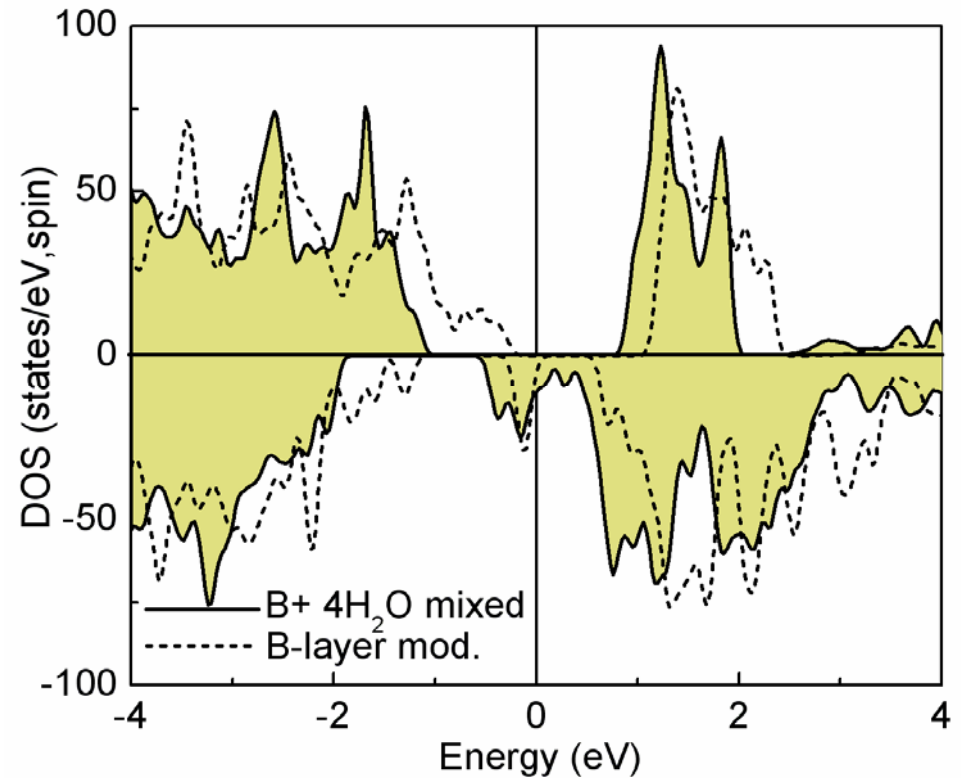
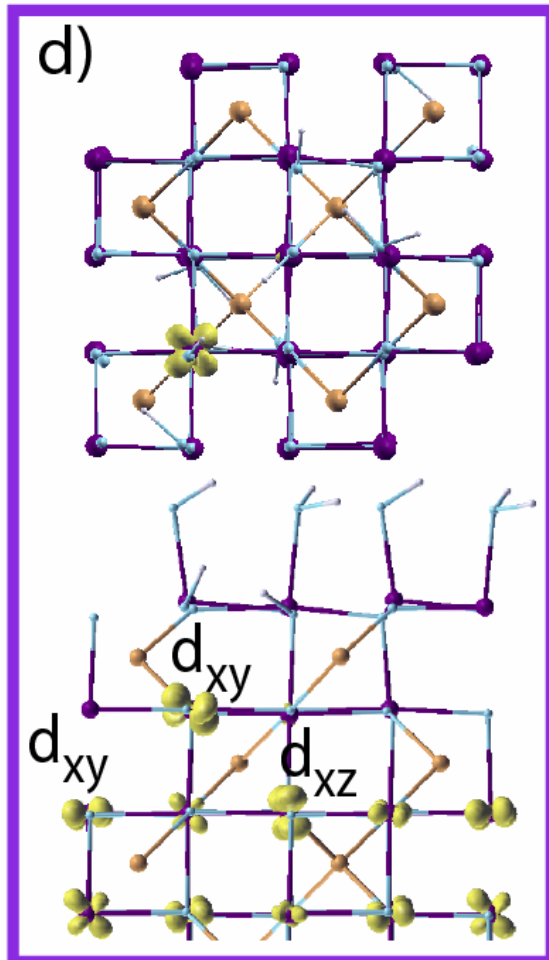


Leonov et al, PRL 2004
 Guo et al, PRL 2004

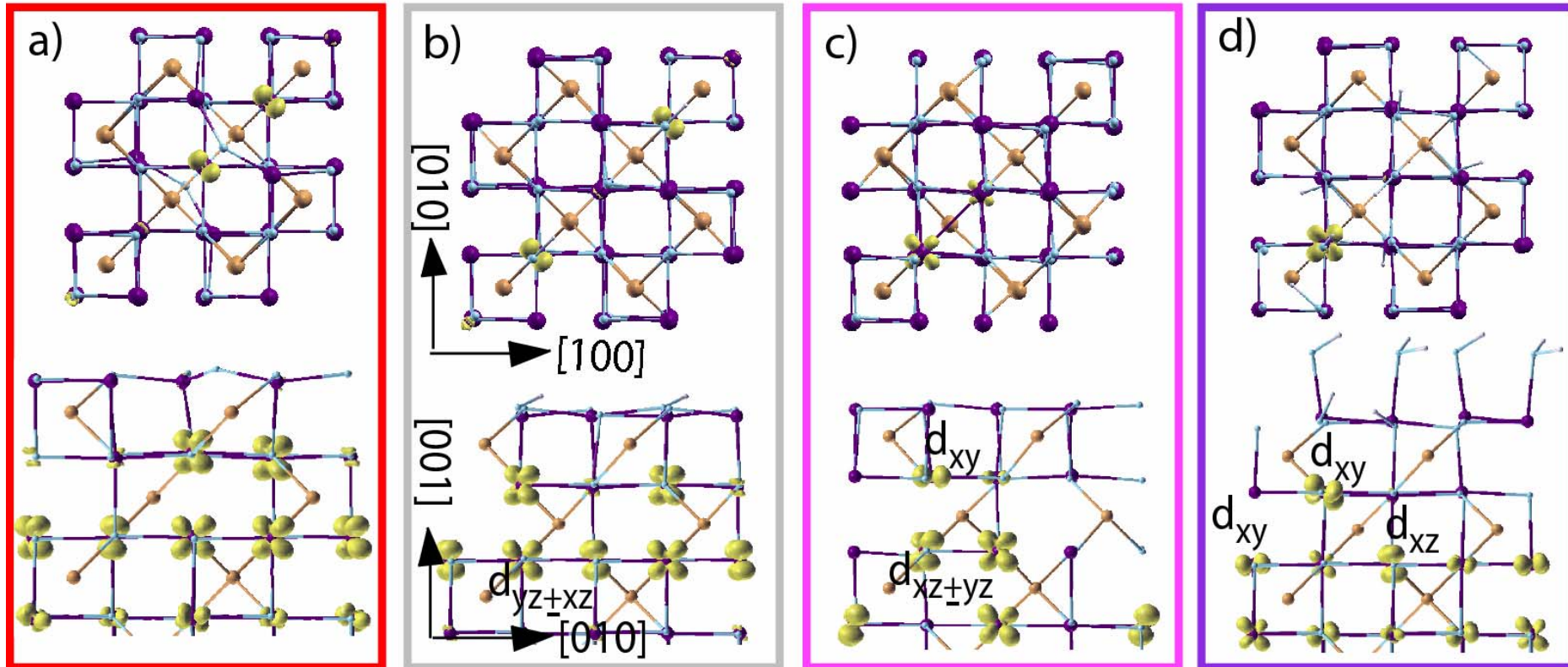


- Clean Fe₃O₄(001)-insulating:
surface STS: $\Delta=0.2$ eV

(Jordan et al. PRB 74, 085416 (2006);
also Lodziana, PRL 99 206402 (2007))



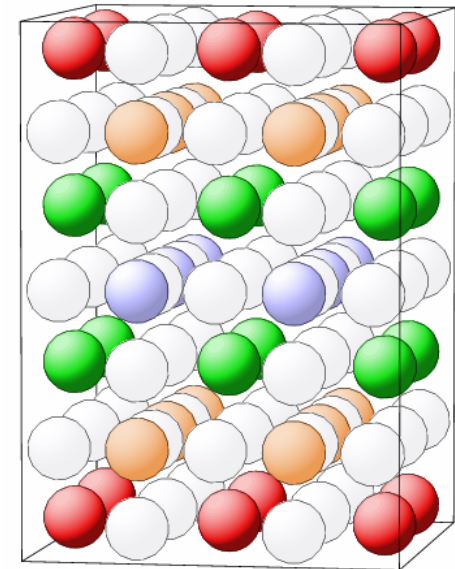
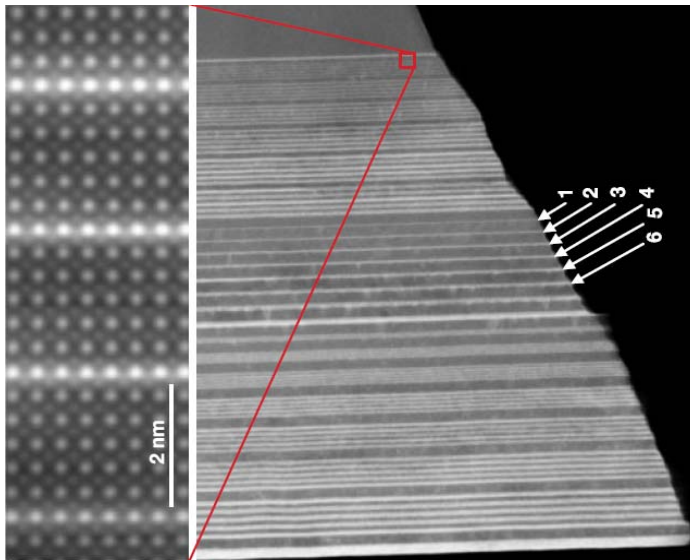
- Insulator to halfmetal transition
(*N. Mulakaluri, RP, et al, PRL 103, 176102 2009*)

Charge and orbital order@ $\text{Fe}_3\text{O}_4(001)$ 

- Surface layer Fe^{3+}
- charge and orbital order in the subsurface layer

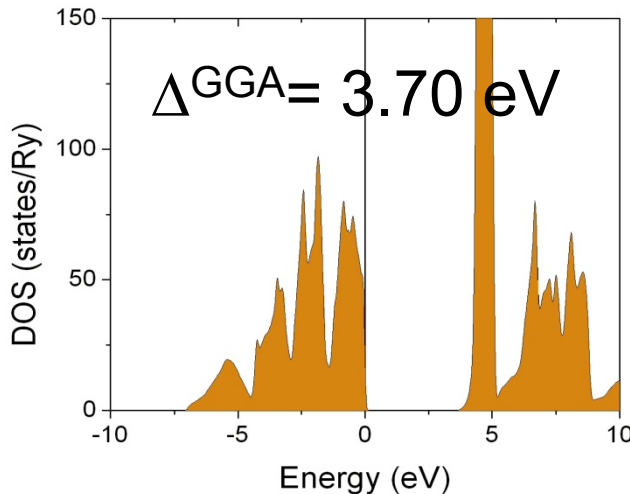
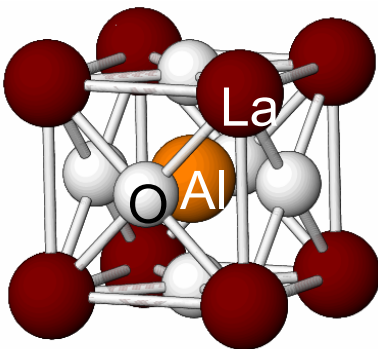
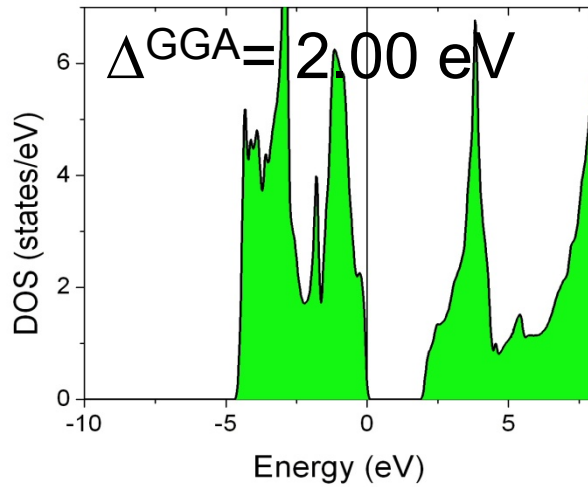
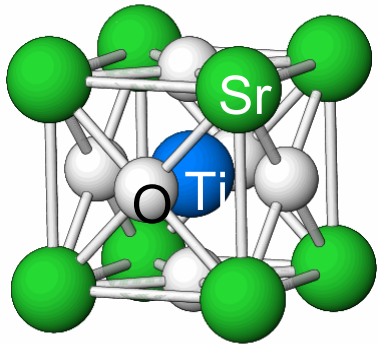
- Isolated molecule: dissociation on defect-free surface and at surface defects
- Higher coverages: crossover to mixed mode of adsorption
- DFT and LEED: suppression of $(\sqrt{2} \times \sqrt{2})R45^\circ$ reconstruction upon water adsorption
- Surfaces and adsorbates (H, H₂O) induce unique CO/OO states

3. Electronic phases at digital perovskite heterostructures: $\text{LaAlO}_3/\text{SrTiO}_3$



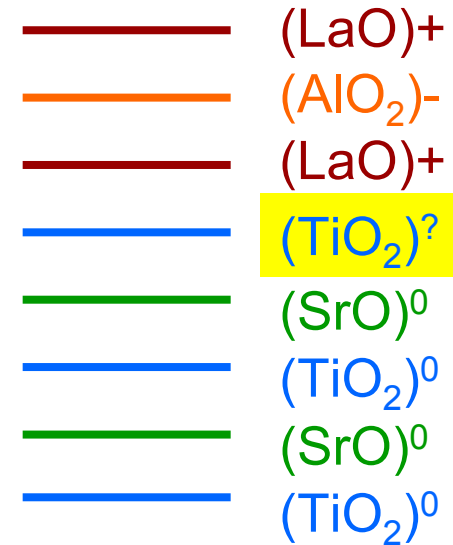
Ohtomo et al., Nature 419, 378 2002

LaAlO₃/SrTiO₃ superlattices

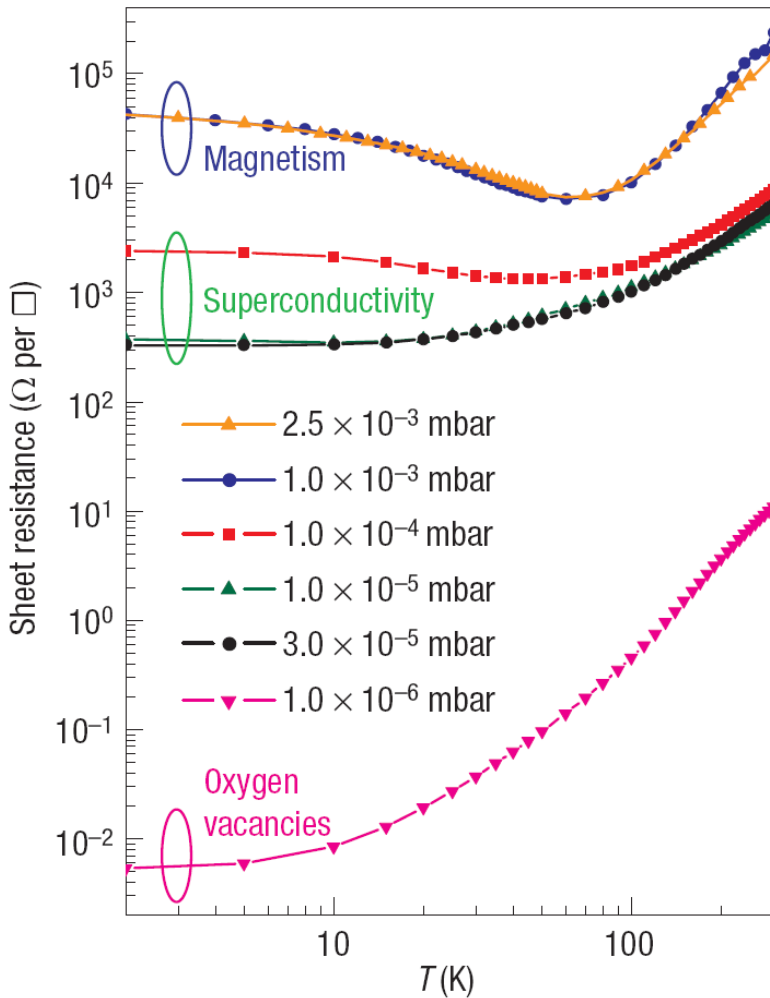


n-type interface

extra ½ electron/IF



- What is the compensation mechanism?
- novel electronic phases?



- magnetism
(Brinkman et al, Nat. Mat. 2007)

- superconductivity
(Reyren et al, Science 2008)

- conductivity
(Ohtomo&Hwang, Nature 2004)

Role of p_{O_2} :

(Nakagawa, Hwang&Muller, Nat. Mat. (2006),

Herranz et al., PRL 2007,

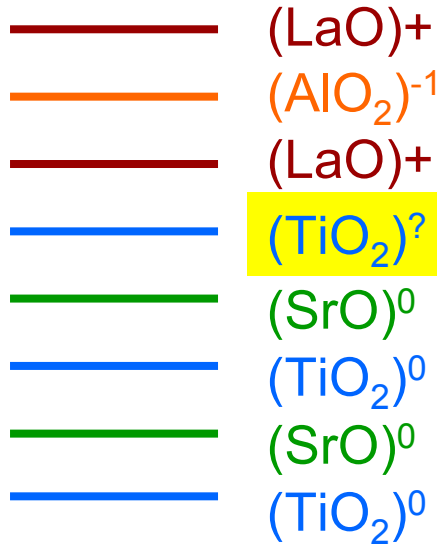
Siemons et al., PRL 2007,

Kalabukhov et al., PRB R, 2007,

(Rijnders&Blank, Nat. Mat. 2008) Basletic et al., Nat. Mat. 2008)



extra $\frac{1}{2}$ electron/IF



- Mechanisms of charge accommodation
- Influence of electronic correlations
- Influence of lattice relaxations

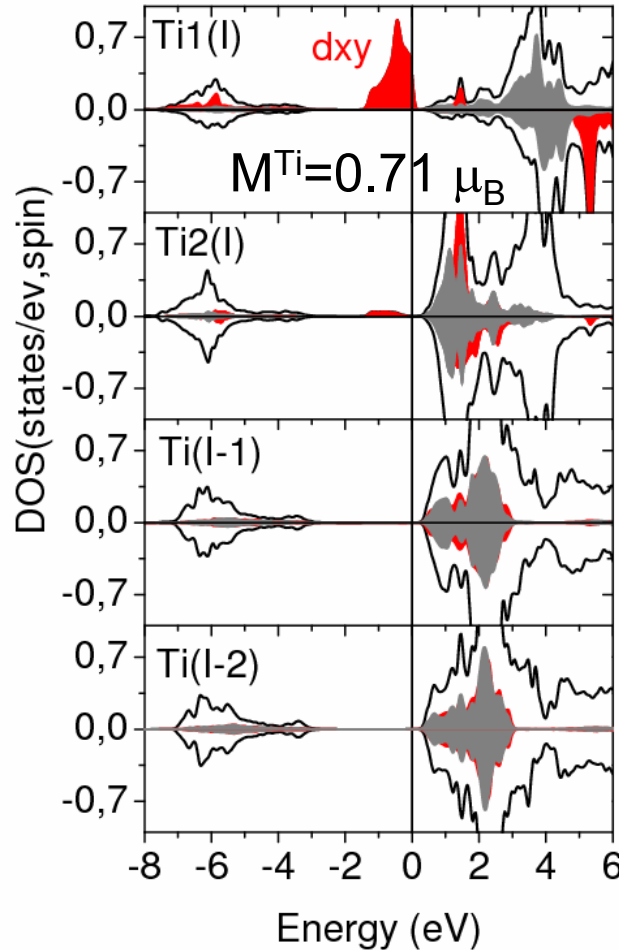
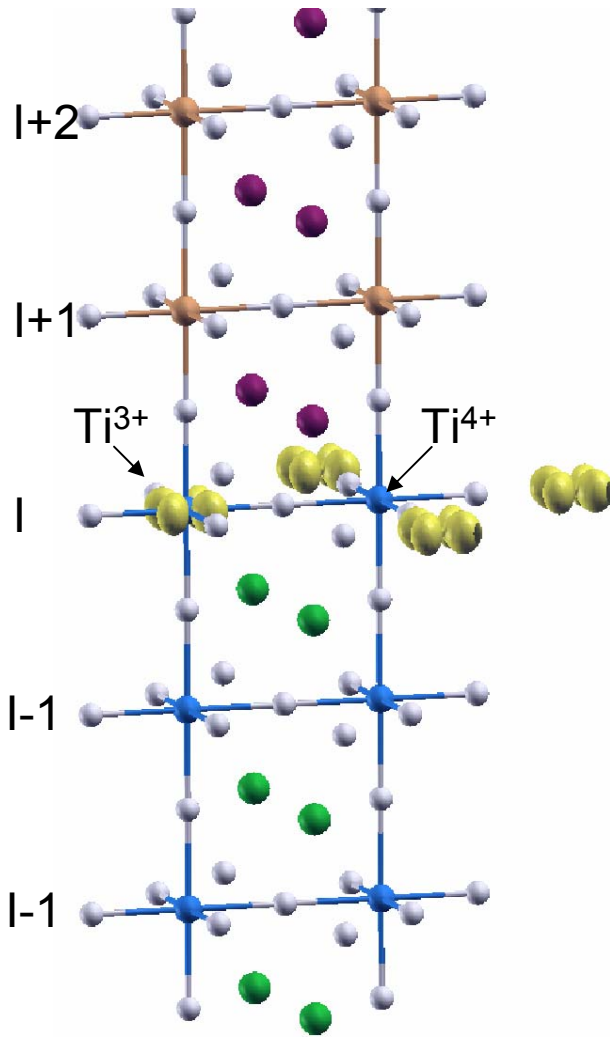
Hubbard modeling
of LTO/STO
by Okamoto and Millis
(*e.g. Nature 428, 630, 2004*)

(n, m) LTO(or LAO)/STO,
($1 \leq n, m \leq 9$):

- WIEN2k code,
- GGA+U
- $c(2 \times 2)$ or $p(2 \times 2)$ -unit cells

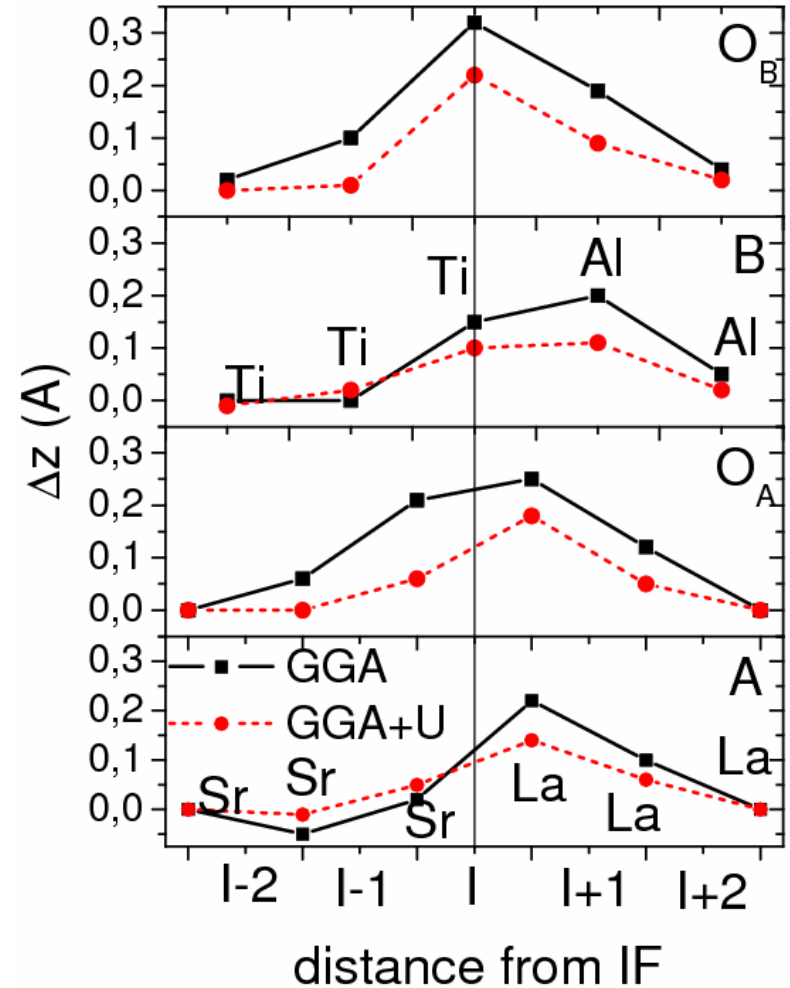
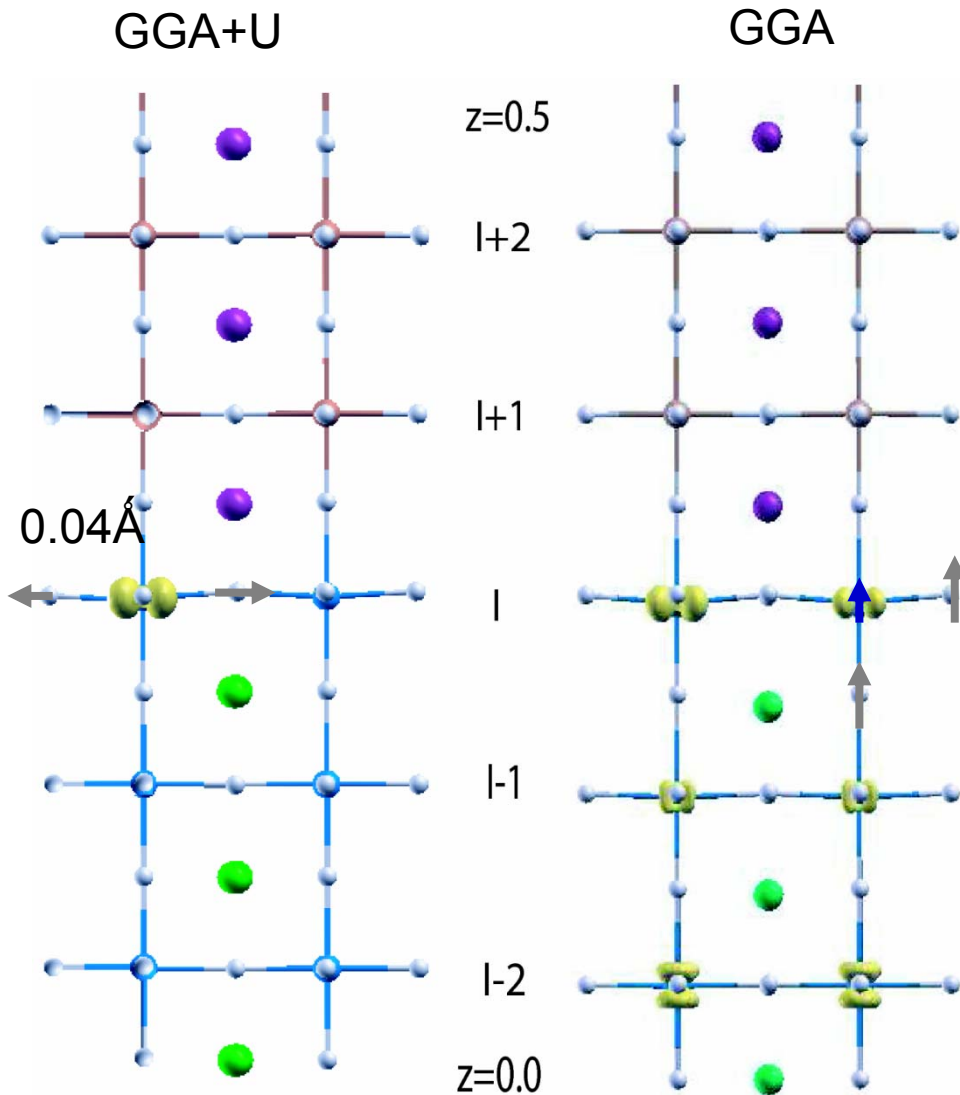


Ideal coordinates

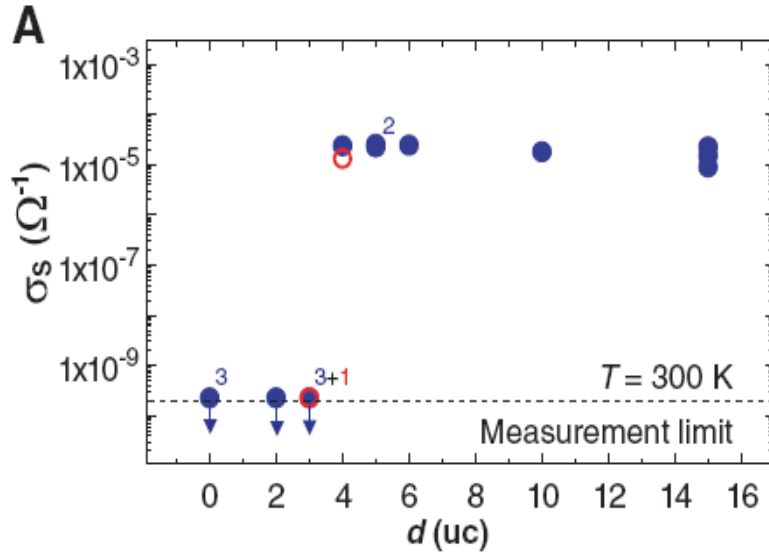


- Ti@IF charge ordered: Ti³⁺ and Ti⁴⁺
- d_{xy} orbital order

Magnetism@IF of nonmagnetic materials

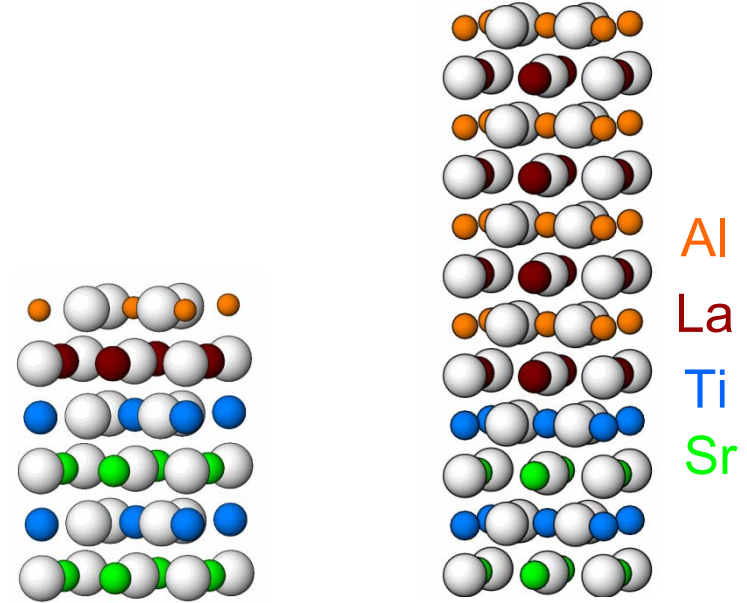


RP&Pickett, PRB 78 2008,
 Popovich et al, PRL 2008
 Zhong&Kelly, EPL 2008



$d_{\text{crit}} = 4 \text{ ML LAO}$
 $d < d_{\text{crit}}$ insulating
 $d \geq d_{\text{crit}}$ conducting

*Thiel, Hammerl, Schmehl,
Schneider&Mannhart,
Science 313 (2006)*



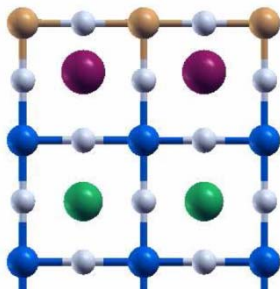
1LAO/STO(001)

4LAO/STO(001)

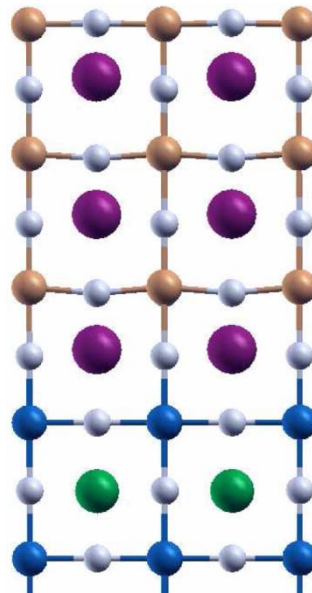
Polar discontinuity both at IF
and surface \rightarrow
how does the proximity to
the surface influence the
electronic properties of the IF:

1LAO/STO(001)

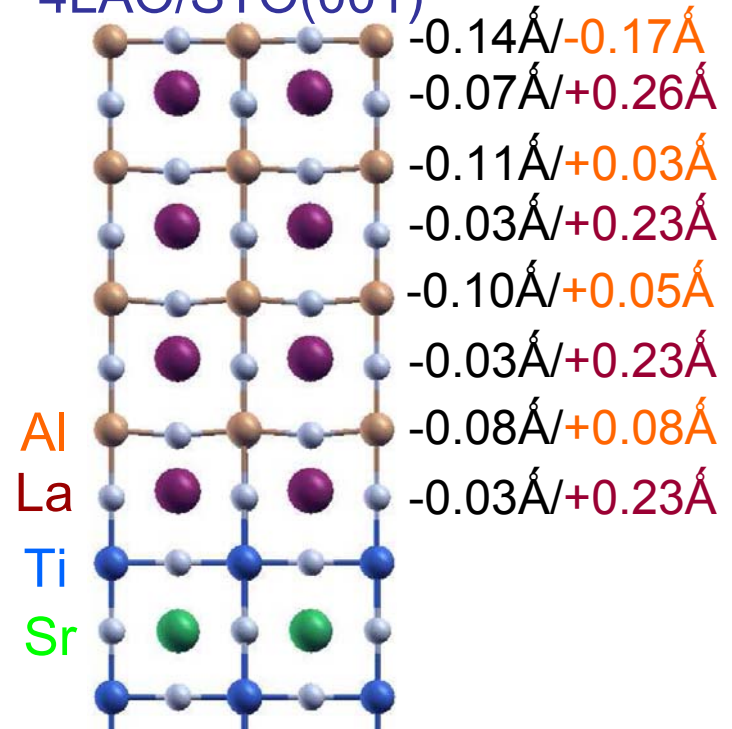
-0.11Å/-0.12Å
-0.01Å/+0.26Å



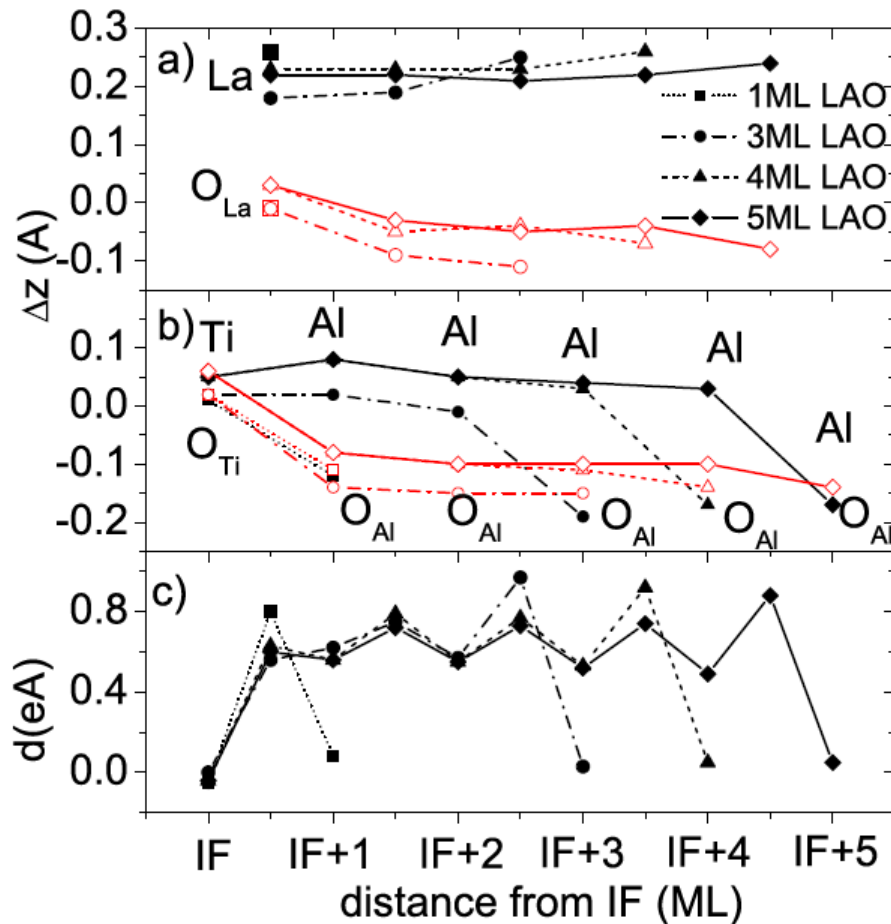
3LAO/STO(001)



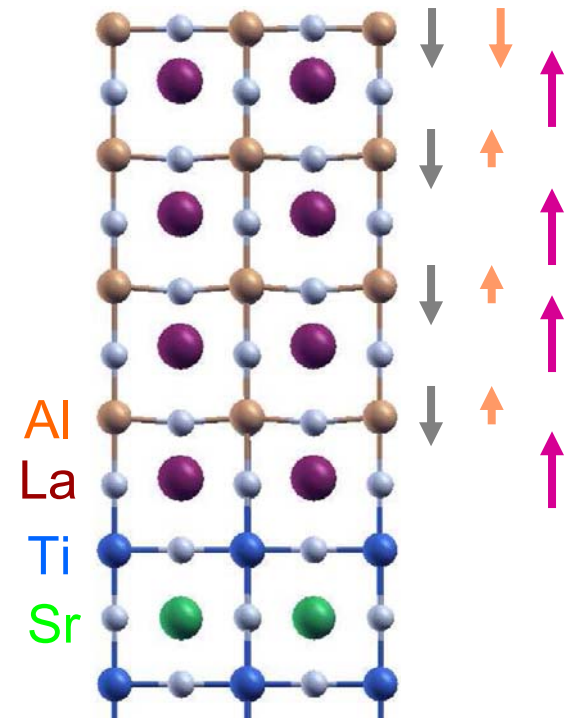
4LAO/STO(001)



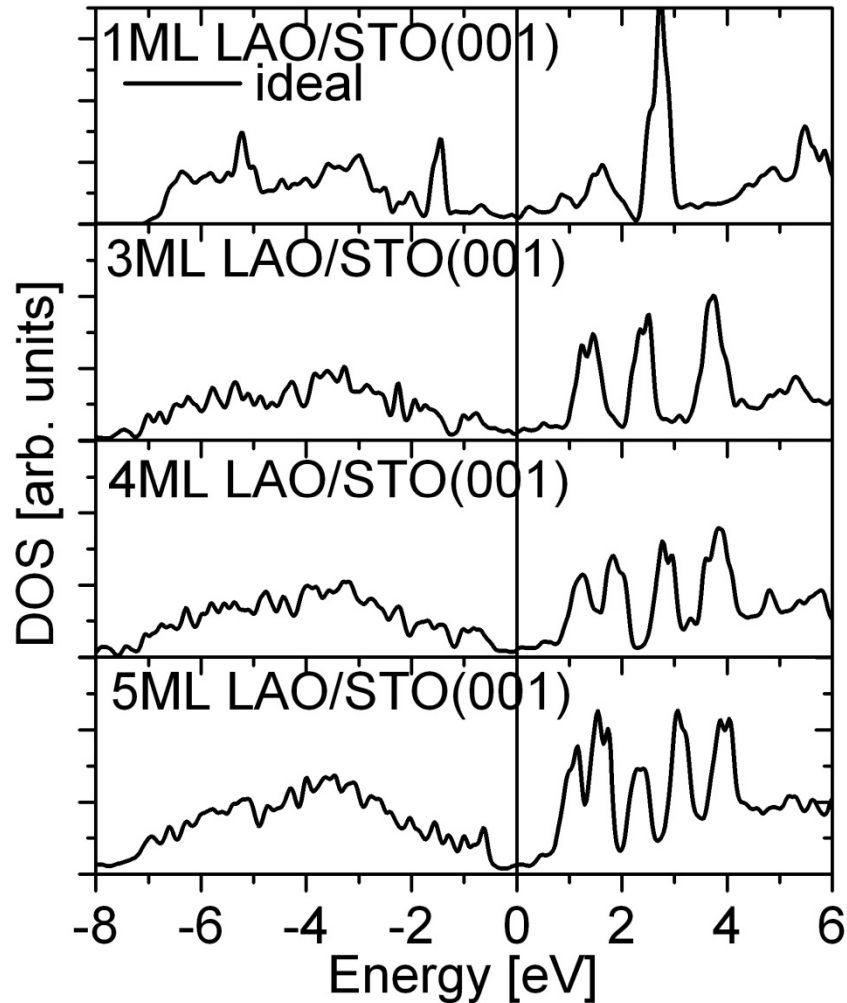
- uniform polar distortion
 - outward shift of La^{3+} of 0.20-0.26 Å
 - response to electric dipole?



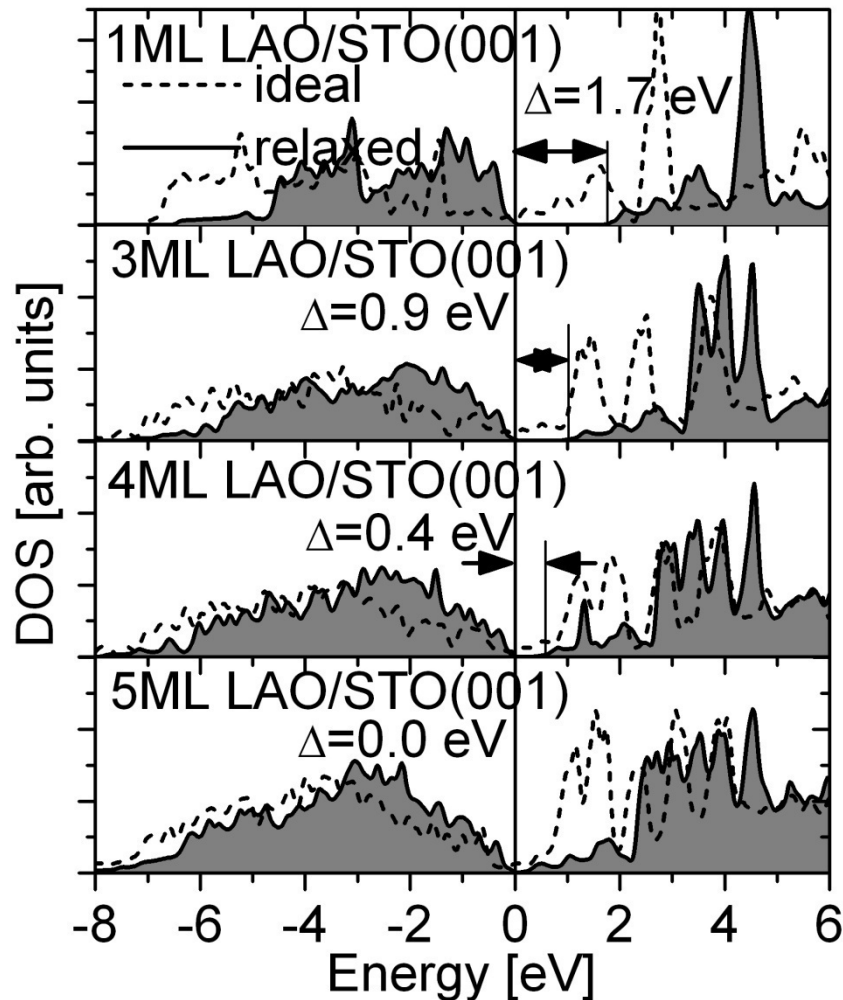
4ML $LaAlO_3$ /
 $SrTiO_3(001)$



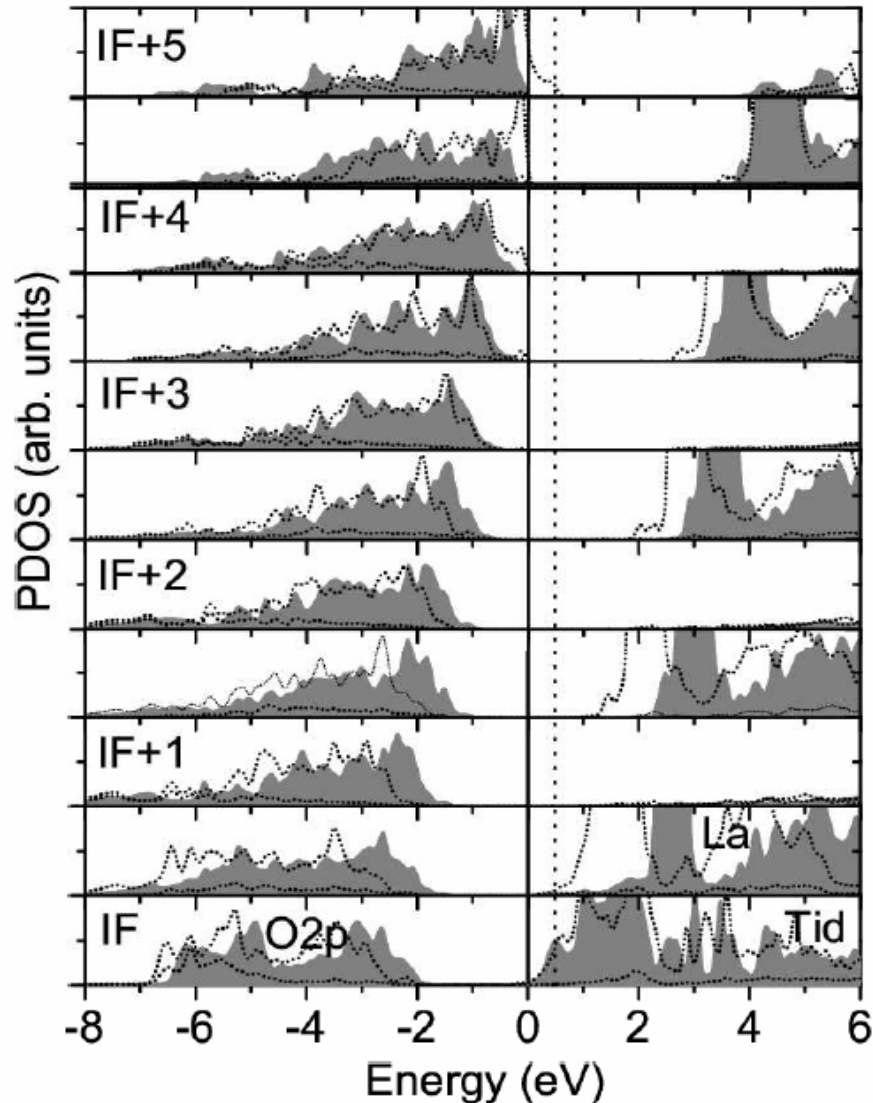
- Dipole shift $D_{bare} \approx -0.5 \times 3.9 \times 4 = -7.8 e\text{\AA}$
- dipole shift due to FE distortion $D_{FE} = \sum Z_i \times \Delta z_i = 4.8 e\text{\AA} = 60\% \times D_{bare}$



- without relaxation –
all systems *metallic*



- without relaxation – all systems *metallic*
- *insulating* behavior due to FE distortion
- reduction of the band gap with increasing number of LAO-layers (~ 0.4 eV/ML)
- closing of the gap at 5ML LAO



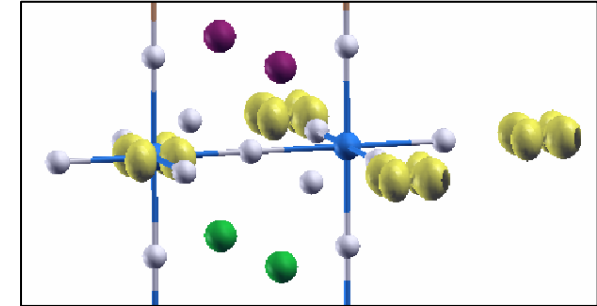
Rigid upward shift of O2p bands

Ideal positions: metallic behavior
with partial occupation of
Ti 3d states@IF

Relaxed structure:
VBM determined by O2p@surface
CBM by Ti 3d states,
Ti remains in 4+

Isolated n -type LAO/STO IF

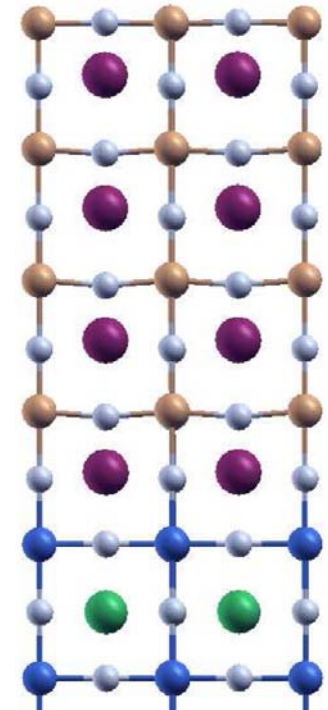
- CO,OO (Ti^{3+} and Ti^{4+})@ IF
- magnetism: (A)FM
- Relaxations -two competing states:
 - GGA: polar distortion - delocalization
 - GGA+U: CO/OO, stronger localization



LAO/STO(001) –surfaces:

- Proximity to the surface matters!
- finite size effects: strong polar distortions in LAO \rightarrow insulating
- thickness dependent insulator-to-metal transition
- crossover to electronic reconstruction $n \geq 5\text{ML}$
- STO capping layer can trigger IMT@2ML LAO

*RP&Pickett, PRB74, 035112 (2006); PRB 78 2008;
PRL 99, 016802 (2007), PRL 102, 107602 (2009),
JPCM 22, 043001 (2010); RP et al, condmat/0912.4671*





Fe₃O₄(001) and H₂O on Fe₃O₄(001):

- N. Mulakaluri, *LMU München*
- M. Scheffler, *FHI, Berlin*
- XRD, LEED:
W. Moritz, *LMU München,*
- PES, STM, XPS:
G. Güntherodt, *RWTH Aachen*
U. Rüdiger, *Uni Konstanz*
U. Diebold, *Tulane University, TU
Wien*
G. E. Brown, *Stanford*

Perovskite interfaces

- W.E. Pickett (UC Davis)
- K. Otte (*LMU München*)
- J. Mannhart (Uni Augsburg)
- A. Brinkman, M. Huijben et al
(U Twente)